

# 2MBI450VJ-120-50

**IGBT Modules** 

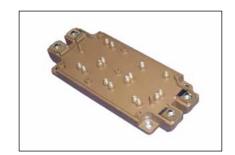
# **IGBT MODULE (V series)** 1200V / 450A / 2 in one package

#### Features

High speed switching Voltage drive Low Inductance module structure

#### Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



## Maximum Ratings and Characteristics

Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items			Symbols	Conditions	Conditions		Units	
	Collector-Emitter voltage		Vces			1200	V	
Inverter	Gate-Emitter voltage		V <sub>GES</sub>			±20	V	
			Ic	Continuous	Tc=25°C	600		
				Continuous	Tc=100°C	450		
			Ic pulse	1ms	1ms		Α	
			-lc					
			-lc pulse	1ms	1ms			
			Pc	1 device	1 device		W	
Junction temperature			Tj			175		
Operating junction temperature (under switching conditions)			Tjop			150	°C	
Case temperature			Tc			125		
Storage temperature			Tstg			-40 to +125		
Isc	plation voltage between terminal and copper base (*1)	V <sub>iso</sub>	AC : 1min.		2500	VAC		
	Diation voitage	between thermistor and others (*2)	Viso	AC . IIIIII.			2300	
Sc	crew torque	Mounting (*3)				3.5		
		Terminals (*4)	]-			4.5	N m	
		PC-Board (*5)				0.6		

Note \*1: All terminals should be connected together during the test.

Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test. Note \*3: Recommendable value : 2.5-3.5 Nm (M5) Note \*4: Recommendable value : 3.5-4.5 Nm (M6) Note \*5: Recommendable value : 0.4-0.6 Nm (M2.5)

### ● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items		Cumbala	Canditions		Characteristics			Haita	
ite	ems	Symbols	Conditions		min.	typ.	max.	Units	
	Zero gate voltage collector current	Ices	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 1200V		-	-	3.0	mA	
	Gate-Emitter leakage current	I <sub>GES</sub>	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	600	nA	
	Gate-Emitter threshold voltage	V <sub>GE (th)</sub>	V <sub>CE</sub> = 20V, I <sub>C</sub> = 450mA		6.0	6.5	7.0	V	
	Collector-Emitter saturation voltage	V	V <sub>GE</sub> = 15V I <sub>C</sub> = 450A	Tj=25°C	-	2.25	2.70	V	
		V <sub>CE</sub> (sat)		Tj=125°C	-	2.55	-		
		(terminal)		Tj=150°C	-	2.60	-		
		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		Tj=25°C	-	1.75	2.20		
		VCE (sat)		Tj=125°C	-	2.05	-		
		(chip)		Tj=150°C	-	2.10	-		
	Internal gate resistance	Rg(int)	-		-	1.67	-	Ω	
		Cies	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz		-	41	-	nF	
	Turn-on time	ton	V <sub>cc</sub> = 600V		- 550 -				
		tr	Ic = 450A		-	180	-		
		tr (i)	V <sub>GE</sub> = ±15V		-	120	-	nsec	
	Turn-off time	toff	$R_G = 0.52\Omega$		-	1050	-	- -	
		tf	L <sub>s</sub> = 80nH		-	110	-		
	Forward on voltage	.,		Tj=25°C	-	2.20	2.65	V	
		V <sub>F</sub>		Tj=125°C	-	2.35	-		
		(terminal)	$V_{GE} = 0V$	Tj=150°C -	-	2.30	-		
		.,	I <sub>F</sub> = 450A	Tj=25°C	-	1.70	2.15		
		V <sub>F</sub>		Tj=125°C	-	1.85	-		
		(chip)		Tj=150°C	-	1.80	-	1	
	Reverse recovery time	trr	I <sub>F</sub> = 450A		-	200	-	nsec	
5			T=25°C		-	5000	-	Ω	
	Resistance	R	T=100°C		465	495	520		
벁	B value	В	T=25/50°C	,	3305	3375	3450	K	

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# ● Thermal resistance characteristics

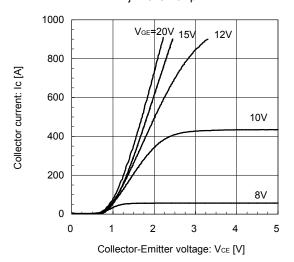
Items	Symbols	Conditions	Characteristics			Units
IIIS			min.	typ.	max.	Units
Thermal registeres (1 device)	Rth(j-c)	Inverter IGBT	-	-	0.066	°C/W
Thermal resistance (1device)		Inverter FWD	-	-	0.100	
Contact thermal resistance (1device) (*6)	Rth(c-f)	with Thermal Compound	-	0.0167	-	

Note  $\star$ 6: This is the value which is defined mounting on the additional cooling fin with thermal compound.

### **■** Characteristics (Representative)

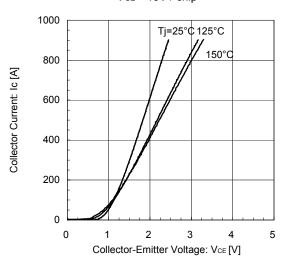
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Tj= 25°C / chip



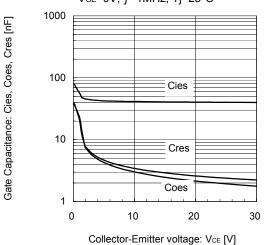
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.)  $V_{GE} = 15V / chip$ 



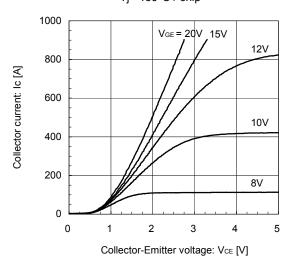
[INVERTER]

Gate Capacitance vs. Collector-Emitter Voltage (typ.) Vge=0V, f=1MHz, Tj=25°C



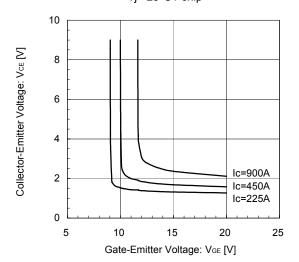
[INVERTER]

Collector current vs. Collector-Emitter voltage (typ.) Ti= 150°C / chip



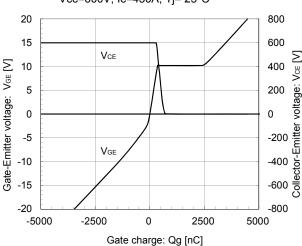
[INVERTER]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.) Tj= 25°C / chip



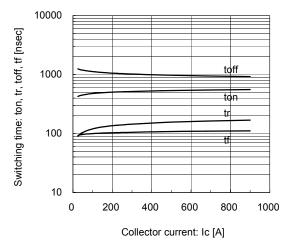
[INVERTER]
Dynamic Gate Charge (typ.)

Vcc=600V, Ic=450A, Tj= 25°C



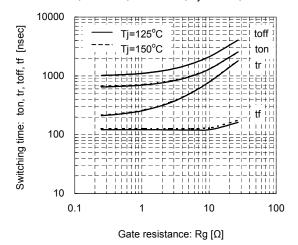
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= $\pm$ 15V, Rg=0.52 $\Omega$ , Tj=25°C



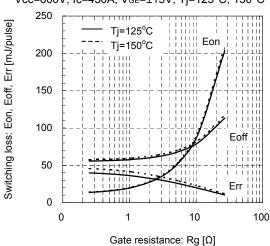
[INVERTER]

Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=450A, V<sub>GE</sub>=±15V, Tj=125°C, 150°C



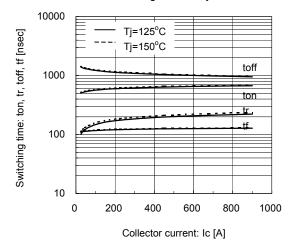
[INVERTER]

Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=450A, V<sub>GE</sub>=±15V, Tj=125°C, 150°C



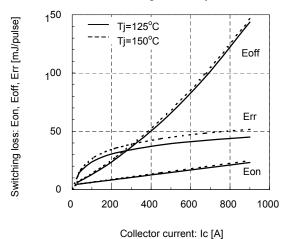
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VGE= $\pm$ 15V, Rg=0.52 $\Omega$ , Tj=125°C, 150°C



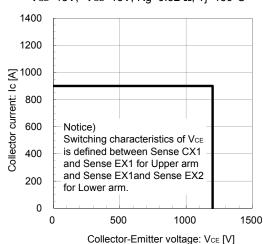
[INVERTER]

Switching loss vs. Collector current (typ.) Vcc=600V, VgE= $\pm$ 15V, Rg=0.52 $\Omega$ , Tj=125°C, 150°C



[INVERTER]

Reverse bias safe operating area (max.) +V<sub>GE</sub>=15V, -V<sub>GE</sub>=15V, Rg=0.52  $\Omega$ , Tj=150°C



[INVERTER] Forward Current vs. Forward Voltage (typ.) chip 1000 800 Forward current: IF [A] Tj=25°C 600 400 125°C 200 150°C 0 0

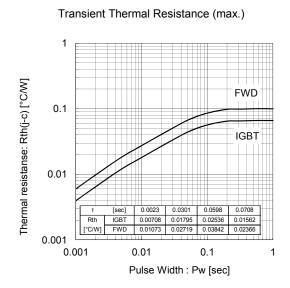
Forward on voltage: VF [V]

Vcc=600V, VgE= $\pm$ 15V, Rg=0.52 $\Omega$ , Tj=25 $^{\circ}$ C 10000 Reverse recovery current: Irr [A] Reverse recovery time: trr [nsec] 1000 Irr trr 100 10 0 200 400 600 800 1000 Forward current: IF [A]

[INVERTER] Reverse Recovery Characteristics (typ.)

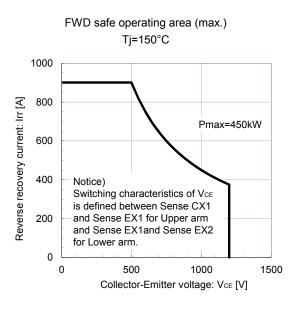
Vcc=600V,  $V_{GE}=\pm15V$ , Rg=0.52Ω, Tj=125°C, 150°C 10000 Tj=125°C Reverse recovery current: Irr [A] Reverse recovery time: trr [nsec] Tj=150°C 1000 Irr 100 10 0 200 400 600 800 1000 Forward current: IF [A]

[INVERTER] Reverse Recovery Characteristics (typ.)

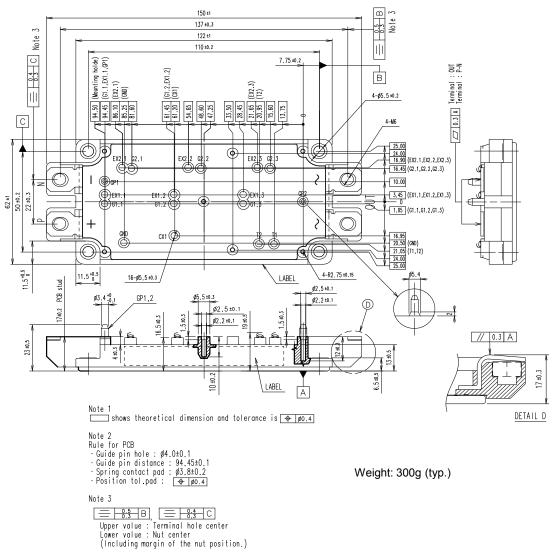


Temperature characteristic (typ.) 100 Resistance : R [kΩ] 10 -60 -40 -20 0 20 40 60 80 100 120 140 160 Temperature [°C]

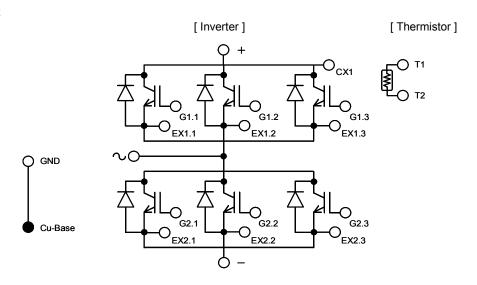
[THERMISTOR]



# ■ Outline Drawings (Unit : mm)



### **■** Equivalent circuit



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